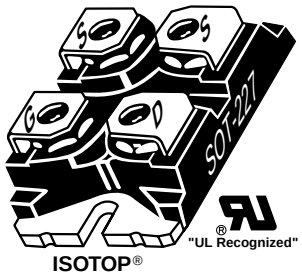
APT30M19JVR

300V 130A 0.019Ω

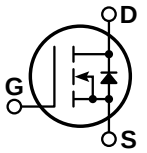
POWER MOS V®

Power MOS V® is a new generation of high voltage N-Channel enhancement mode power MOSFETs. This new technology minimizes the JFET effect, increases packing density and reduces the on-resistance. Power MOS V® also achieves faster switching speeds through optimized gate layout.



ISOTOP®

- **Faster Switching**
- **100% Avalanche Tested**
- **Lower Leakage**
- **Popular SOT-227 Package**



MAXIMUM RATINGS All Ratings: T_C = 25°C unless otherwise specified.

Symbol	Parameter	APT30M19JVR	UNIT
V_{DSS}	Drain-Source Voltage	300	Volts
I_D	Continuous Drain Current @ T_C = 25°C	130	Amps
I_{DM}	Pulsed Drain Current ①	520	
V_{GS}	Gate-Source Voltage Continuous	±30	Volts
V_{GSM}	Gate-Source Voltage Transient	±40	
P_D	Total Power Dissipation @ T_C = 25°C	700	Watts
	Linear Derating Factor	5.6	W/°C
T_J,T_{STG}	Operating and Storage Junction Temperature Range	-55 to 150	°C
T_L	Lead Temperature: 0.063" from Case for 10 Sec.	300	
I_{AR}	Avalanche Current ① (Repetitive and Non-Repetitive)	130	Amps
E_{AR}	Repetitive Avalanche Energy ①	50	mJ
E_{AS}	Single Pulse Avalanche Energy ④	3600	

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-Source Breakdown Voltage (V_{GS} = 0V, I_D = 250μA)	300			Volts
$I_{D(on)}$	On State Drain Current ② ($V_{DS} > I_{D(on)} \times R_{DS(on)}$ Max, V_{GS} = 10V)	130			Amps
$R_{DS(on)}$	Drain-Source On-State Resistance ② (V_{GS} = 10V, 0.5 $I_{D[Cont.]}$)			0.019	Ohms
I_{DSS}	Zero Gate Voltage Drain Current ($V_{DS} = V_{DSS}$, V_{GS} = 0V)			100	μA
	Zero Gate Voltage Drain Current (V_{DS} = 0.8 V_{DSS}, V_{GS} = 0V, T_C = 125°C)			500	
I_{GSS}	Gate-Source Leakage Current (V_{GS} = ±30V, V_{DS} = 0V)			±100	nA
$V_{GS(th)}$	Gate Threshold Voltage ($V_{DS} = V_{GS}$, I_D = 5.0mA)	2		4	Volts

CAUTION: These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

APT Website - http://www.advancedpower.com

USA
405 S.W. Columbia Street **Bend, Oregon 97702-1035** **Phone: (541) 382-8028** **FAX: (541) 388-0364**
EUROPE
Avenue J.F. Kennedy Bât B4 Parc Cadéra Nord **F-33700 Merignac - France** **Phone: (33) 5 57 92 15 15** **FAX: (33) 5 56 47 97 61**

050-5585 Rev B

DYNAMIC CHARACTERISTICS

APT30M19JVR

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
C_{iss}	Input Capacitance	V_{GS} = 0V V_{DS} = 25V f = 1 MHz		18000	21600	pF
C_{oss}	Output Capacitance			3250	4550	
C_{rss}	Reverse Transfer Capacitance			980	1470	
Q_g	Total Gate Charge ③	V_{GS} = 10V V_{DD} = 0.5 V_{DSS} I_D = 0.5 $I_{D[Cont.]}$ @ 25°C		650	975	nC
Q_{gs}	Gate-Source Charge			115	175	
Q_{gd}	Gate-Drain ("Miller") Charge			290	435	
$t_{d(on)}$	Turn-on Delay Time	V_{GS} = 15V V_{DD} = 0.5 V_{DSS} I_D = $I_{D[Cont.]}$ @ 25°C R_G = 0.6Ω		22	44	ns
t_r	Rise Time			33	66	
$t_{d(off)}$	Turn-off Delay Time			70	135	
t_f	Fall Time			10	20	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
I_S	Continuous Source Current (Body Diode)			130	Amps
I_{SM}	Pulsed Source Current ① (Body Diode)			520	
V_{SD}	Diode Forward Voltage ② (V_{GS} = 0V, I_S = -$I_{D[Cont.]}$)			1.3	Volts
t_{rr}	Reverse Recovery Time (I_S = -$I_{D[Cont.]}$, dI_S/dt = 100A/µs)		620		ns
Q_{rr}	Reverse Recovery Charge (I_S = -$I_{D[Cont.]}$, dI_S/dt = 100A/µs)		14		µC

THERMAL / PACKAGE CHARACTERISTICS

Symbol	Characteristic	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to Case			0.18	°C/W
$R_{\theta JA}$	Junction to Ambient			40	
$V_{Isolation}$	RMS Voltage (50-60 Hz Sinusoidal Waveform From Terminals to Mounting Base for 1 Min.)	2500			Volts
Torque	Maximum Torque for Device Mounting Screws and Electrical Terminations.			13	lb•in

① Repetitive Rating: Pulse width limited by maximum junction temperature.

② Pulse Test: Pulse width < 380 µS, Duty Cycle < 2%

③ See MIL-STD-750 Method 3471

④ Starting T_j = +25°C, L = 426µH, R_G = 25Ω, Peak I_L = 130A

APT Reserves the right to change, without notice, the specifications and information contained herein.

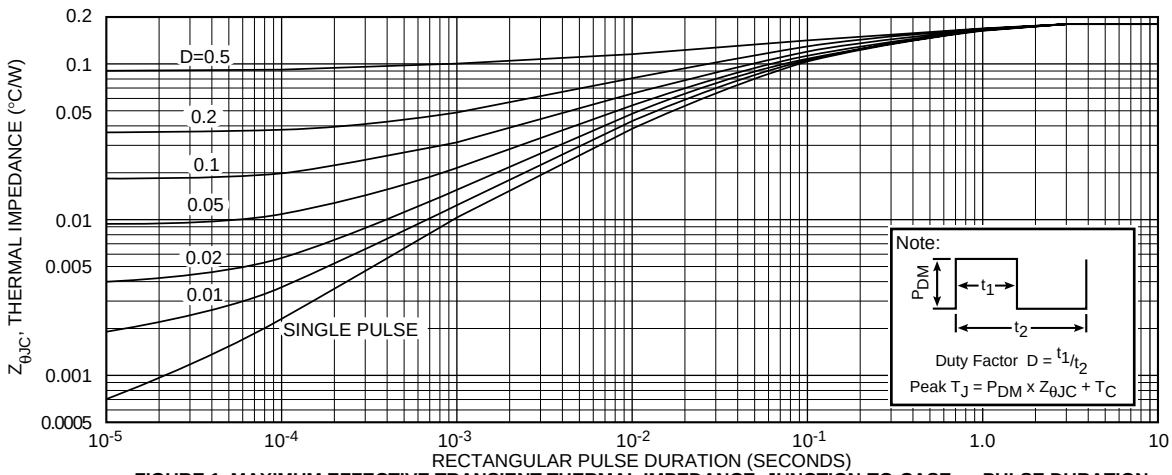


FIGURE 1, MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs PULSE DURATION

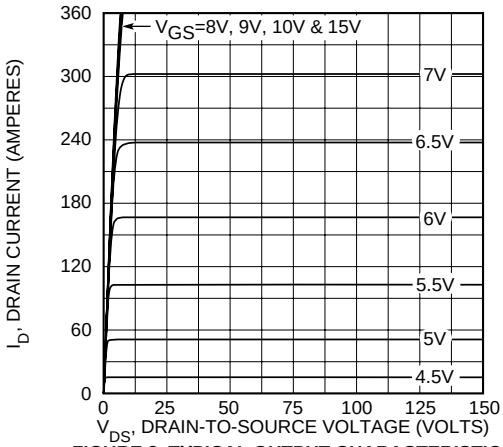


FIGURE 2, TYPICAL OUTPUT CHARACTERISTICS

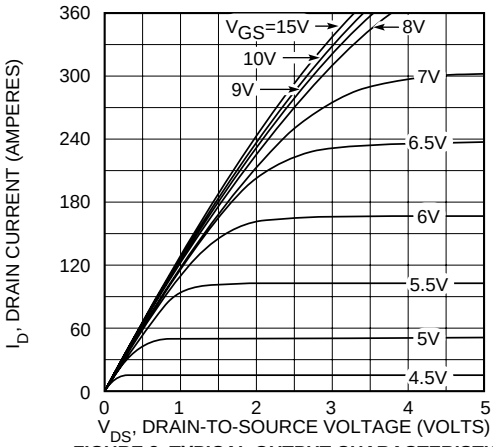


FIGURE 3, TYPICAL OUTPUT CHARACTERISTICS

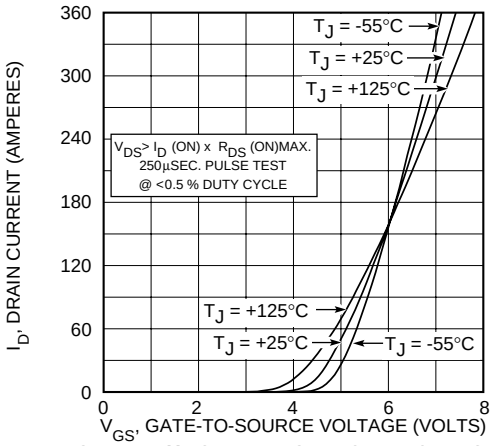


FIGURE 4, TYPICAL TRANSFER CHARACTERISTICS

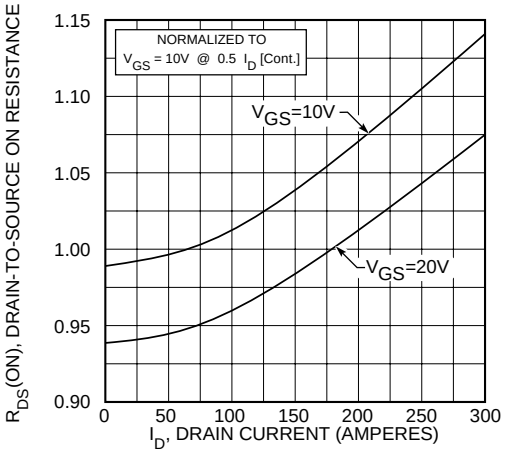


FIGURE 5, R_{DS}(ON) vs DRAIN CURRENT

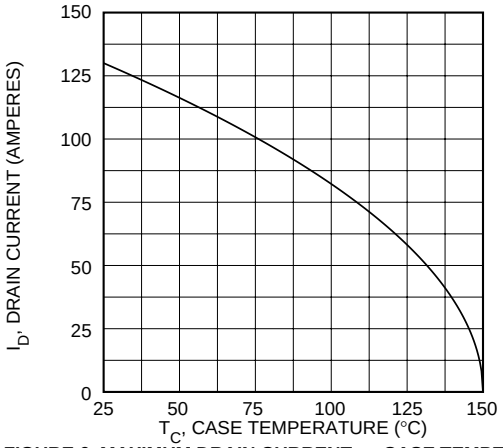


FIGURE 6, MAXIMUM DRAIN CURRENT vs CASE TEMPERATURE

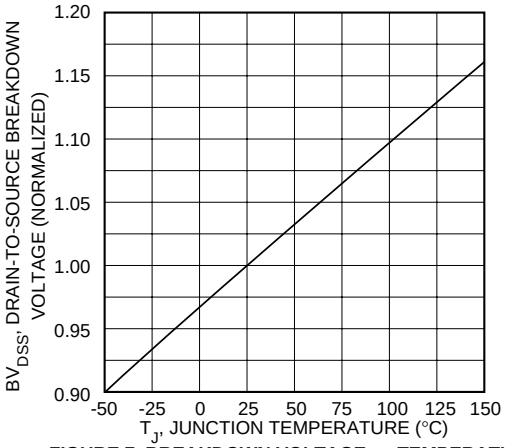


FIGURE 7, BREAKDOWN VOLTAGE vs TEMPERATURE

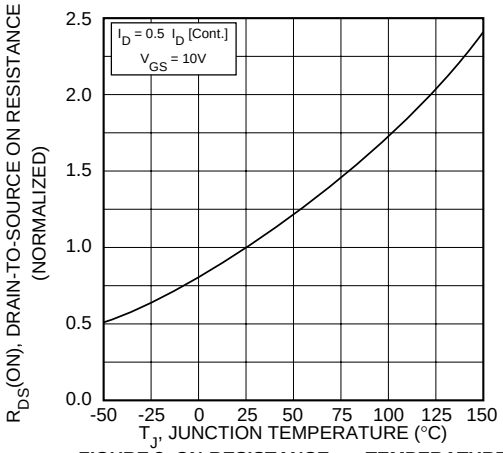


FIGURE 8, ON-RESISTANCE vs. TEMPERATURE

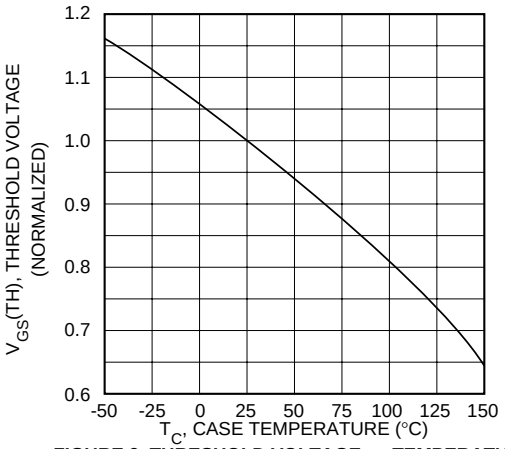


FIGURE 9, THRESHOLD VOLTAGE vs TEMPERATURE

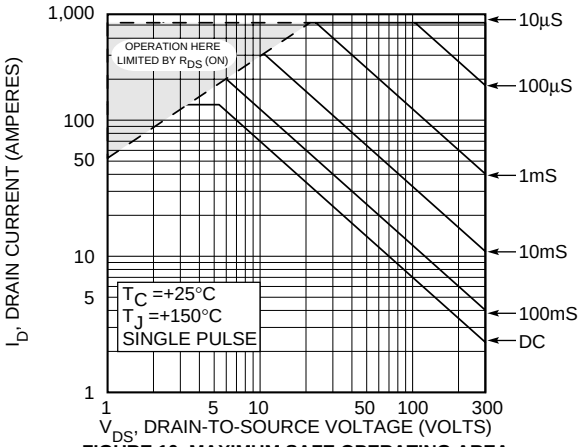


FIGURE 10, MAXIMUM SAFE OPERATING AREA

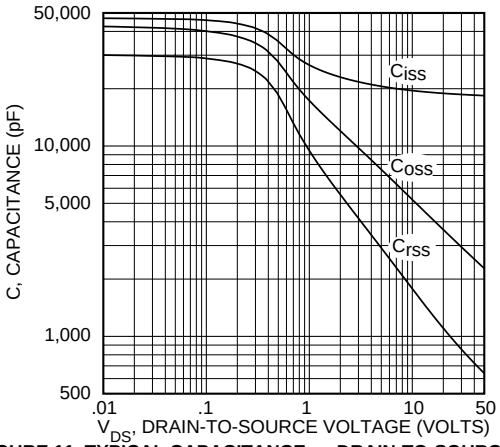


FIGURE 11, TYPICAL CAPACITANCE vs DRAIN-TO-SOURCE VOLTAGE

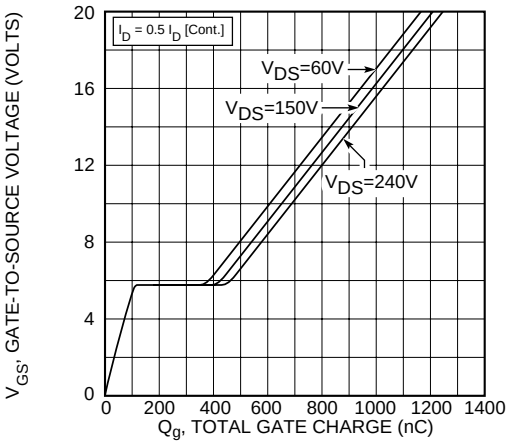


FIGURE 12, GATE CHARGES vs GATE-TO-SOURCE VOLTAGE

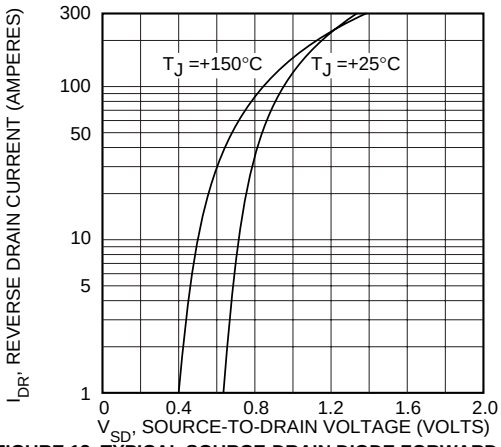
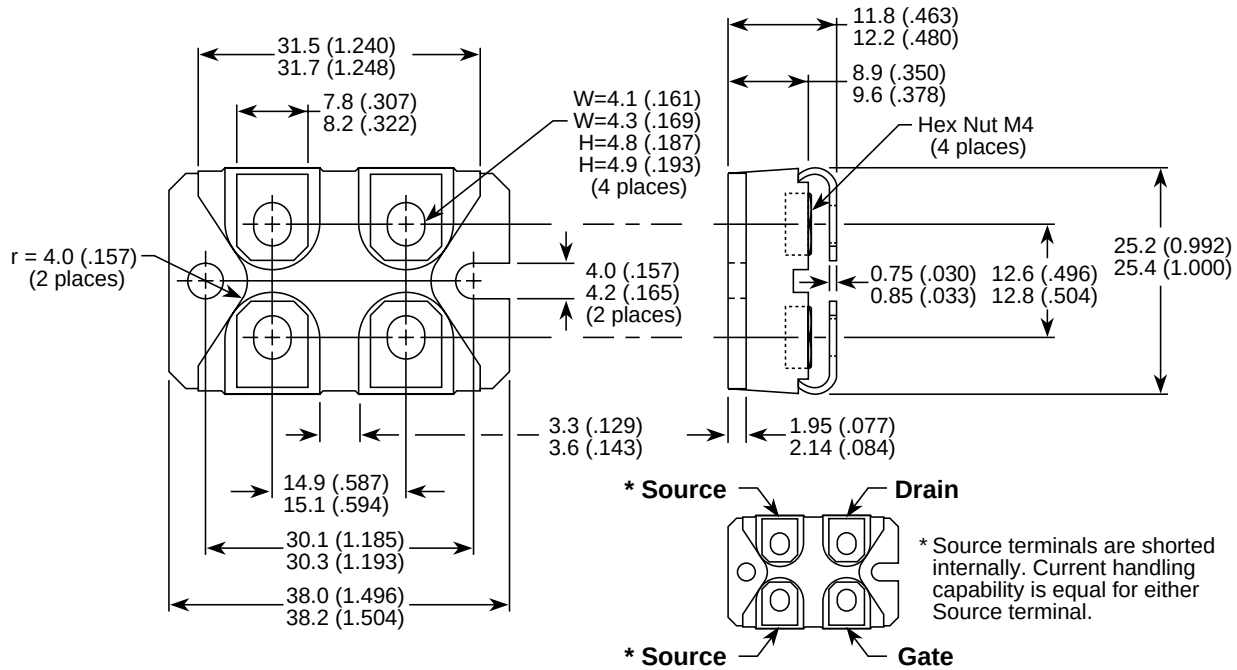


FIGURE 13, TYPICAL SOURCE-DRAIN DIODE FORWARD VOLTAGE

SOT-227 (ISOTOP®) Package Outline



Dimensions in Millimeters and (Inches)

$V_{Isolation}$, RMS Voltage (50-60 Hz Sinusoidal Waveform from Terminals to Mounting Base for 1 Minute) = 2500 Volts Minimum

ISOTOP® is a Registered Trademark of SGS Thomson.

"UL Recognized" File No. E145592

APT's devices are covered by one or more of the following U.S.patents: 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058